

HUFA76404DK8T

N-Channel Dual MOSFET

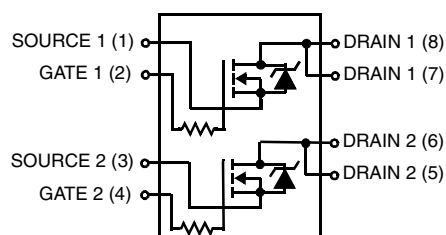
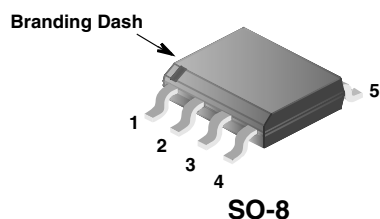
62V, 3.2A, 132mΩ

Features

- $r_{DS(ON)} = 110m\Omega$ (Typ.), $V_{GS} = 5V$, $I_D = 3.2A$
- $Q_{g(tot)} = 3.8nC$ (Typ.), $V_{GS} = 5V$
- Low Miller Charge
- Low Q_{RR} Body Diode
- Optimized efficiency at high frequencies
- UIS Capability (Single Pulse and Repetitive Pulse)
- Internal $R_G = 100\Omega$
- Qualified to AEC Q101

Applications

- Motor / Body Load Control
- ABS Systems
- Powertrain Management
- Injection Systems
- DC-DC converters and Off-line UPS
- Distributed Power Architectures and VRMs
- Primary Switch for 12V and 24V systems



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	62	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current		
	Continuous ($T_A = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$, $R_{\theta JA} = 50^\circ\text{C/W}$)	3.6	A
	Continuous ($T_A = 25^\circ\text{C}$, $V_{GS} = 5\text{V}$, $R_{\theta JA} = 50^\circ\text{C/W}$)	3.2	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	128	mJ
P_D	Power dissipation	2.5	W
	Derate above 25°C	20	mW/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Pad Area = 0.50 in^2 (323 mm^2) (Note 2)	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Pad Area = 0.027 in^2 (17.4 mm^2) (Note 3)	170	$^\circ\text{C/W}$
$R_{\theta JA}$	Pad Area = 0.006 in^2 (3.87 mm^2) (Note 4)	183	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
76404DK8	HUFA76404DK8T	SO-8	330mm	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	62	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 55\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
		$V_{DS} = 50\text{V}$, $V_{GS} = 0\text{V}$, $T_A = 150^\circ\text{C}$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	1	-	3	V
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = 3.6\text{A}$, $V_{GS} = 10\text{V}$	-	0.088	0.110	Ω
		$I_D = 3.2\text{A}$, $V_{GS} = 5\text{V}$	-	0.110	0.132	

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	250	-	pF
C_{OSS}	Output Capacitance		-	80	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	7	-	pF
R_G	Gate Resistance	$V_{GS} = 0.5\text{V}$, $f = 1\text{MHz}$	-	100	-	Ω
$Q_{g(tot)}$	Total Gate Charge at 5V	$V_{GS} = 0\text{V}$ to 5V	-	3.8	4.9	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0\text{V}$ to 1V	-	0.3	0.4	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 30\text{V}$ $I_D = 3.6\text{A}$ $I_g = 1.0\text{mA}$	-	0.8	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	0.5	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	1.7	-	nC

Switching Characteristics ($V_{GS} = 10V$)

t_{ON}	Turn-On Time	$V_{DD} = 30V, I_D = 3.6A$ $V_{GS} = 10V, R_{GS} = 47\Omega$	-	-	65	ns
$t_{d(ON)}$	Turn-On Delay Time		-	13	-	ns
t_r	Rise Time		-	26	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	145	-	ns
t_f	Fall Time		-	53	-	ns
t_{OFF}	Turn-Off Time		-	-	330	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 3.6A$	-	-	1.25	V
		$I_{SD} = 1.8A$	-	-	1.0	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 3.6A, dI_{SD}/dt = 100A/\mu s$	-	-	37	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 3.6A, dI_{SD}/dt = 100A/\mu s$	-	-	38	nC

Notes:

- 1: Starting $T_J = 25^\circ C$, $L = 41mH$, $I_{AS} = 2.5A$, $V_{DD} = 62V$, $V_{GS} = 10V$.
- 2: $50^\circ C/W$ measured using FR-4 board with $0.50 in^2$ ($323 mm^2$) copper pad at 1 second.
- 3: $170^\circ C/W$ measured using FR-4 board with $0.027 in^2$ ($17.4 mm^2$) copper pad at 1000 seconds.
- 4: $183^\circ C/W$ measured using FR-4 board with $0.006 in^2$ ($3.87 mm^2$) copper pad at 1000 seconds.

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: <http://www.aecouncil.com/>

All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

Typical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

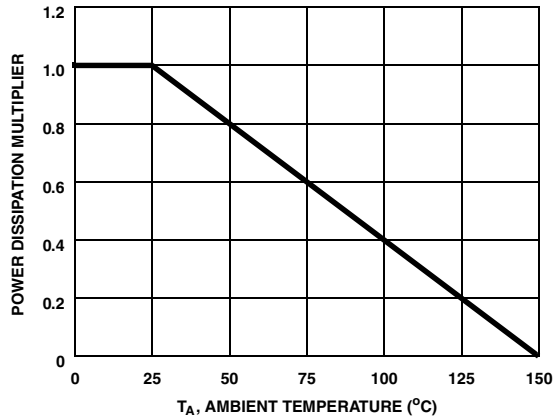


Figure 1. Normalized Power Dissipation vs Ambient Temperature

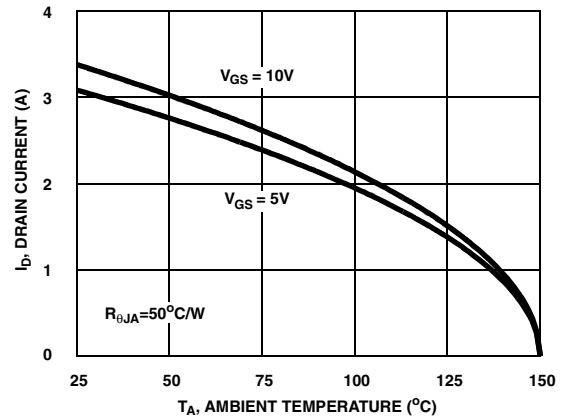


Figure 2. Maximum Continuous Drain Current vs Ambient Temperature

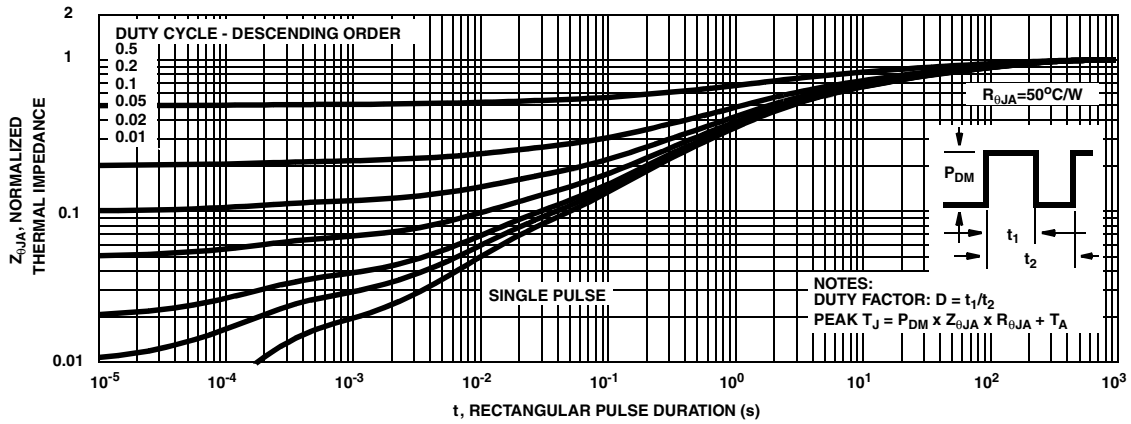


Figure 3. Normalized Maximum Transient Thermal Impedance

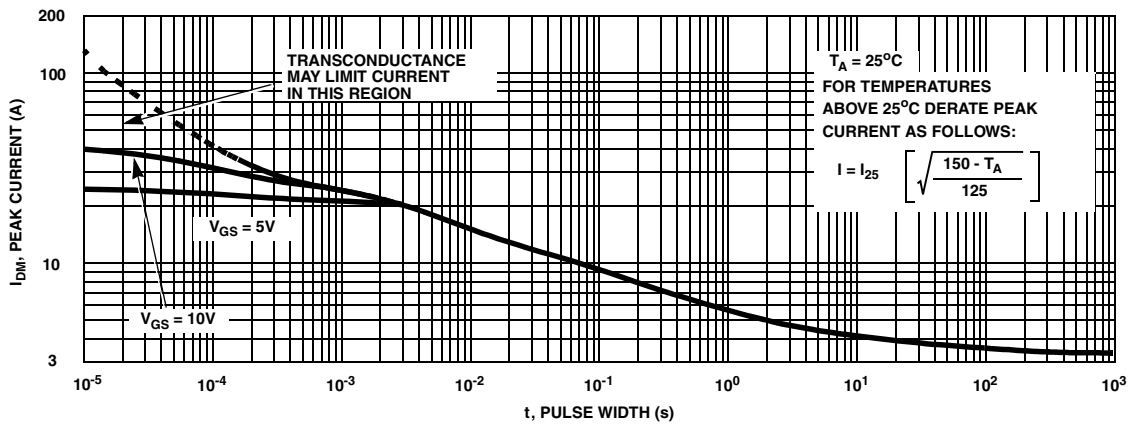


Figure 4. Peak Current Capability

Typical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

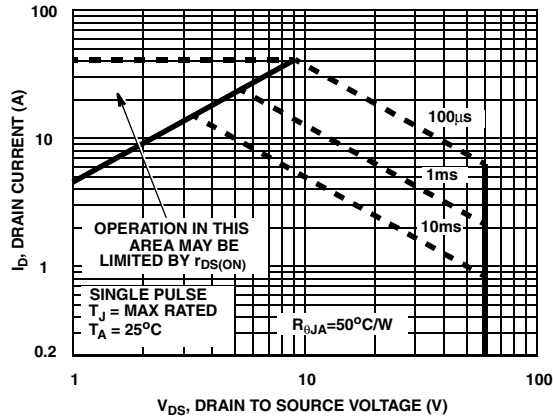


Figure 5. Forward Bias Safe Operating Area

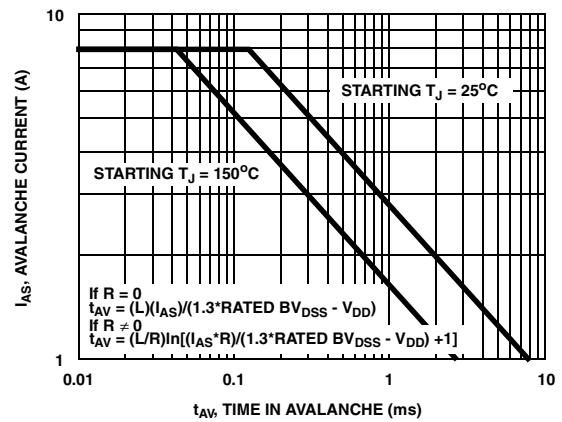


Figure 6. Unclamped Inductive Switching Capability

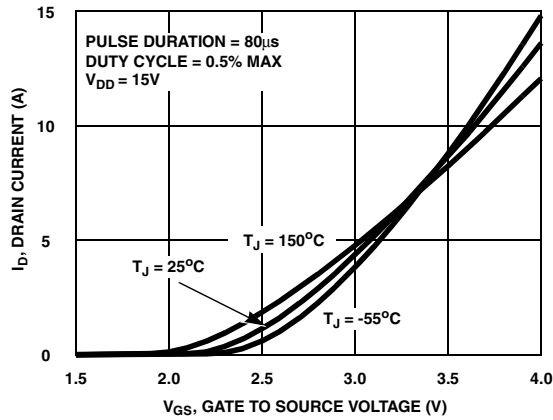


Figure 7. Transfer Characteristics

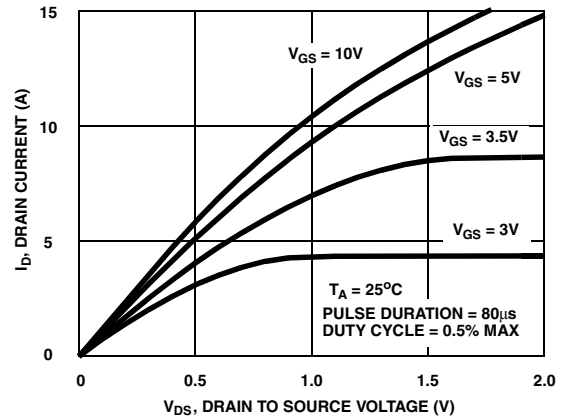


Figure 8. Saturation Characteristics

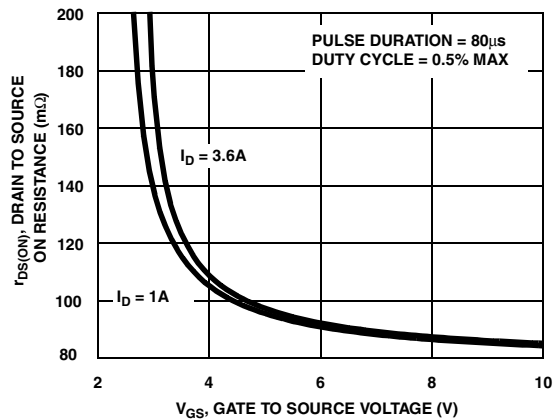


Figure 9. Drain to Source On Resistance vs Gate Voltage and Drain Current

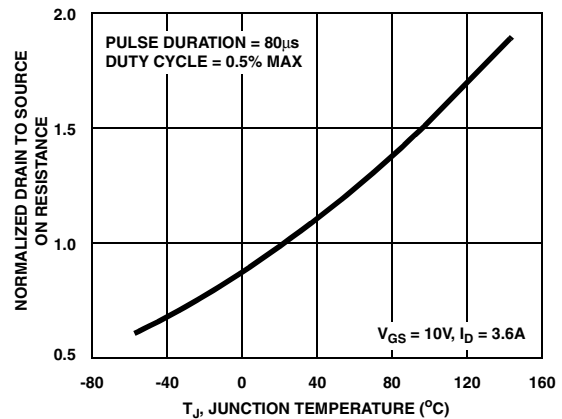


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

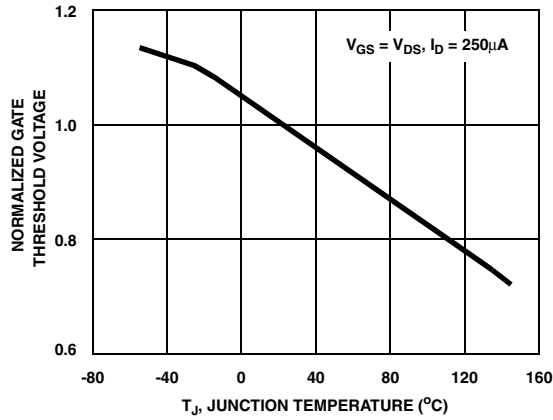


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

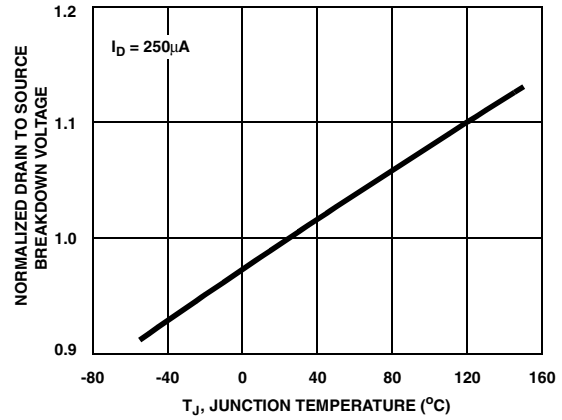


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

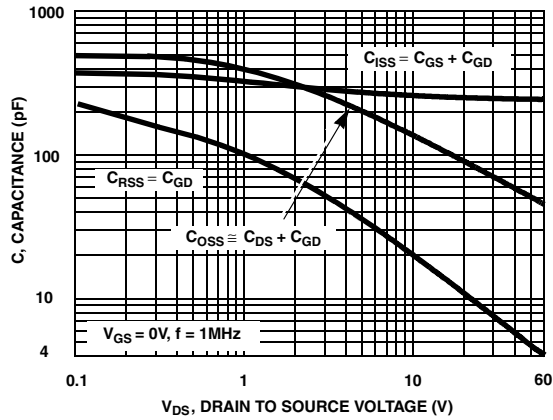


Figure 13. Capacitance vs Drain to Source Voltage

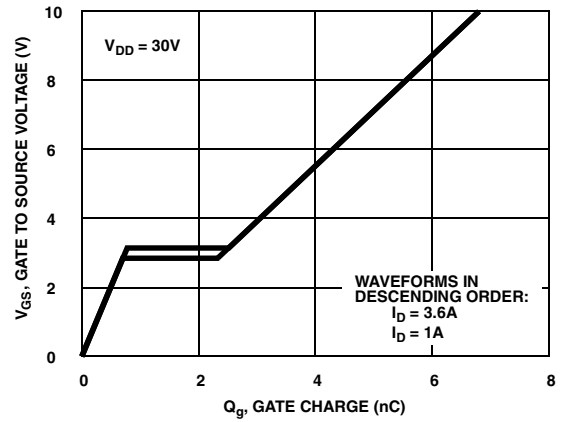


Figure 14. Gate Charge Waveforms for Constant Gate Currents

Thermal Resistance vs. Mounting Pad Area

The maximum rated junction temperature, T_{JM} , and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation, P_{DM} , in an application. Therefore the application's ambient temperature, T_A ($^{\circ}\text{C}$), and thermal resistance $R_{\theta JA}$ ($^{\circ}\text{C}/\text{W}$) must be reviewed to ensure that T_{JM} is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{R_{\theta JA}} \quad (\text{EQ. 1})$$

In using surface mount devices such as the SO8 package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of P_{DM} is complex and influenced by many factors:

1. Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
2. The number of copper layers and the thickness of the board.
3. The use of external heat sinks.
4. The use of thermal vias.
5. Air flow and board orientation.
6. For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Figure 21 defines the $R_{\theta JA}$ for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the Fairchild device Spice thermal model or manually utilizing the normalized

maximum transient thermal impedance curve.

Thermal resistances corresponding to other copper areas can be obtained from Figure 21 or by calculation using Equation 2. The area, in square inches is the top copper area including the gate and source pads.

$$R_{\theta JA} = 79.9 + \frac{15}{0.14 + \text{Area}} \quad (\text{EQ. 2})$$

The transient thermal impedance ($Z_{\theta JA}$) is also effected by varied top copper board area. Figure 22 shows the effect of copper pad area on single pulse transient thermal impedance. Each trace represents a copper pad area in square inches corresponding to the descending list in the graph. Spice and SABER thermal models are provided for each of the listed pad areas.

Copper pad area has no perceivable effect on transient thermal impedance for pulse widths less than 100ms. For pulse widths less than 100ms the transient thermal impedance is determined by the die and package. Therefore, CHERM1 through CHERM5 and RHERM1 through RHERM5 remain constant for each of the thermal models. A listing of the model component values is available in Table 1.

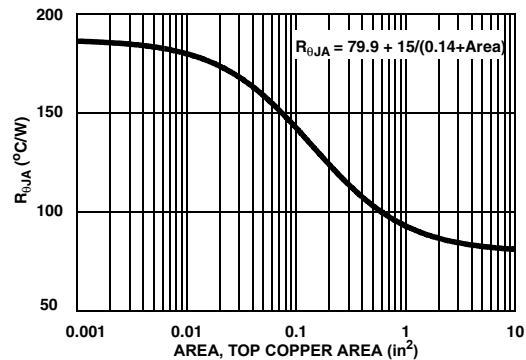


Figure 21. Thermal Resistance vs Mounting Pad Area

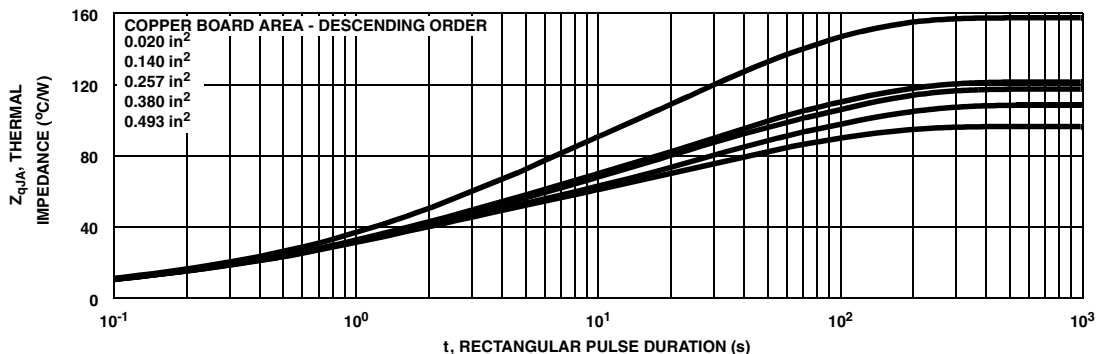


Figure 22. Thermal Impedance vs Mounting Pad Area

Test Circuits and Waveforms

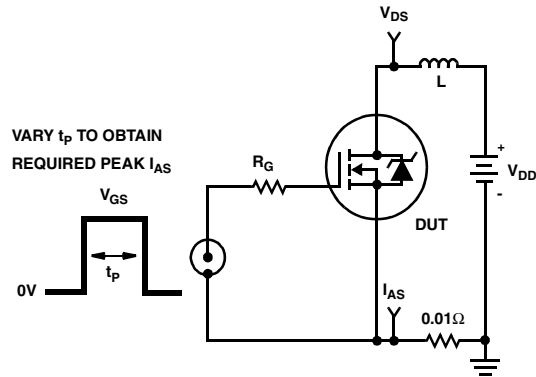


Figure 15. Unclamped Energy Test Circuit

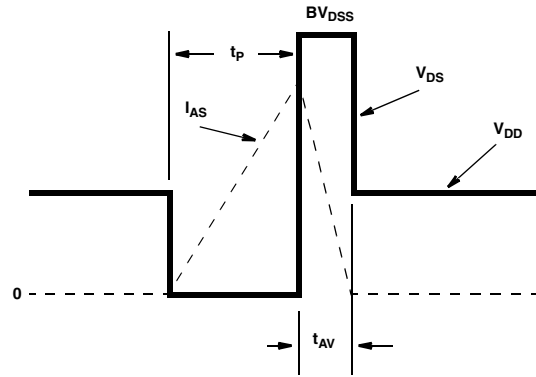


Figure 16. Unclamped Energy Waveforms

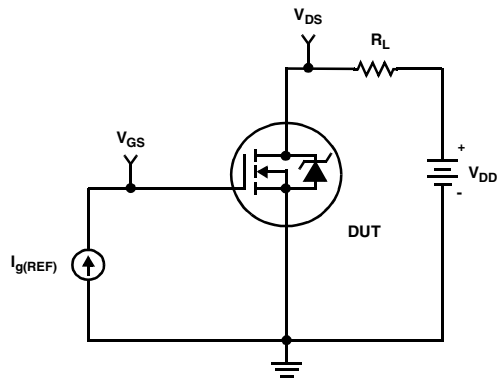


Figure 17. Gate Charge Test Circuit

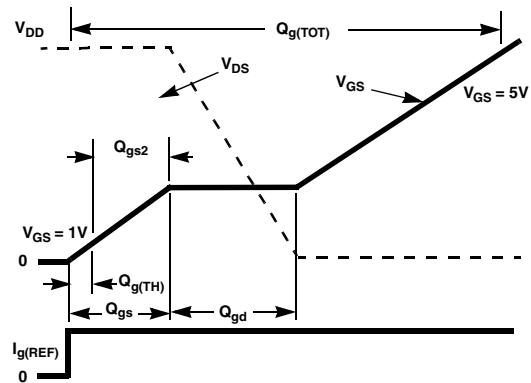


Figure 18. Gate Charge Waveforms

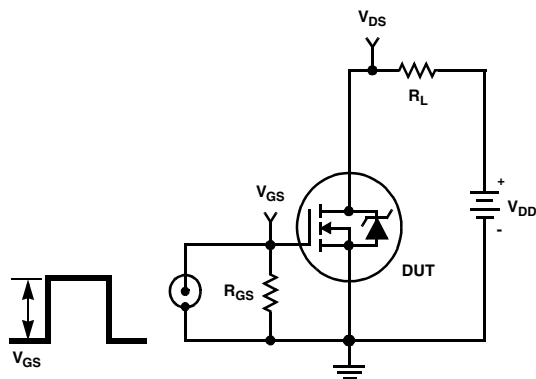


Figure 19. Switching Time Test Circuit

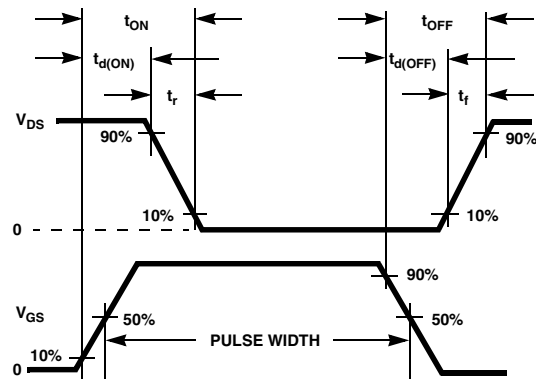


Figure 20. Switching Time Waveforms

PSPICE Electrical Model

.SUBCKT HUF76404DK8T 2 1 3 ; rev March 2004

Ca 12 8 3.8e-10

Cb 15 14 3.8e-10

Cin 6 8 2.6e-10

Dbody 7 5 DbodyMOD

Dbreak 5 11 DbreakMOD

Dplcap 10 5 DplcapMOD

Ebreak 11 7 17 18 62.5

Eds 14 8 5 8 1

Egs 13 8 6 8 1

Esg 6 10 6 8 1

Evthres 6 21 19 8 1

Etemp 20 6 18 22 1

It 8 17 1

Lgate 1 9 2.22e-9

Ldrain 2 5 1.0e-9

Lsource 3 7 0.93e-9

RLgate 1 9 22.2

RLdrain 2 5 10

RLsource 3 7 9.3

Mmed 16 6 8 8 MmedMOD

Mstro 16 6 8 8 MstroMOD

Mweak 16 21 8 8 MweakMOD

Rbreak 17 18 RbreakMOD 1

Rdrain 50 16 RdrainMOD 2.4e-2

Rgate 9 20 103.3

RSLC1 5 51 RSLCMOD 1.0e-6

RSLC2 5 50 1.0e3

Rsource 8 7 RsourceMOD 5.4e-2

Rvthres 22 8 RvthresMOD 1

Rvtemp 18 19 RvtempMOD 1

S1a 6 12 13 8 S1AMOD

S1b 13 12 13 8 S1BMOD

S2a 6 15 14 13 S2AMOD

S2b 13 15 14 13 S2BMOD

Vbat 22 19 DC 1

ESLC 51 50 VALUE={{(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*18),3.7))}}

.MODEL DbodyMOD D (IS=1.1E-12 N=1.03 RS=2.7e-2 TRS1=5.0e-4 TRS2=1.3e-6
+ CJO=6.82e-10 M=0.85 TT=1.6e-8 XTI=4.0)

.MODEL DbreakMOD D (RS=1.65 TRS1=1.0e-3 TRS2=-9e-6)

.MODEL DplcapMOD D (CJO=1.7e-10 IS=1.0e-30 N=10 M=0.85)

.MODEL MstroMOD NMOS (VTO=2.13 KP=19 IS=1e-30 N=10 TOX=1 L=1u W=1u T_ABS=25)

.MODEL MmedMOD NMOS (VTO=1.81 KP=1.08 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=103.3 T_ABS=25)

.MODEL MweakMOD NMOS (VTO=1.59 KP=0.04 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=103.3e1 RS=0.1 T_ABS=25)

.MODEL RbreakMOD RES (TC1=1.12e-3 TC2=-3e-7)

.MODEL RdrainMOD RES (TC1=1.0e-2 TC2=5e-5)

.MODEL RSLCMOD RES (TC1=2.8e-3 TC2=1.9e-5)

.MODEL RsourceMOD RES (TC1=4e-3 TC2=1e-6)

.MODEL RvthresMOD RES (TC1=-2.1e-3 TC2=-3.3e-6)

.MODEL RvtempMOD RES (TC1=-1.6e-3 TC2=1.0e-6)

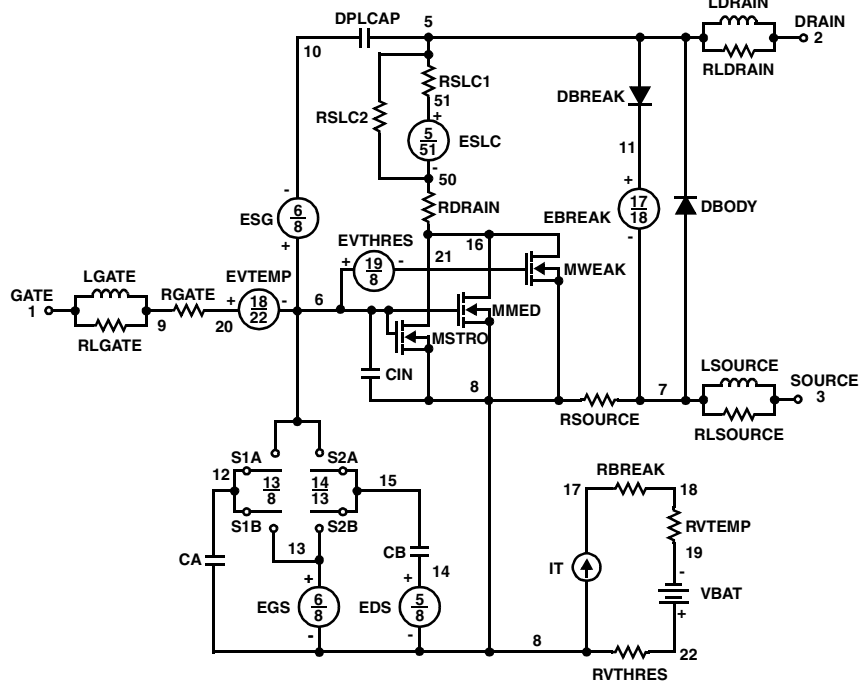
.MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-4 VOFF=-1)

.MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-1 VOFF=-4)

.MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-0.5 VOFF=0.5)

.MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=0.5 VOFF=-0.5)

.ENDS

Note: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.


HUFA76404DK8T N-Channel Dual MOSFET

HUFA76404DK8T Rev. B

SPICE Thermal Model

REV March 2004
HUFA76404DK8T
Copper Area =0.5 in²

CTHERM1 TH 8 1.2e-4
CTHERM2 8 7 4.6e-3
CTHERM3 7 6 5.0e-3
CTHERM4 6 5 1.6e-2
CTHERM5 5 4 4.5e-2
CTHERM6 4 3 1.3e-1
CTHERM7 3 2 6.7e-1
CTHERM8 2 TL 5.5

RTHERM1 TH 8 1.55
RTHERM2 8 7 1.9
RTHERM3 7 6 2.8
RTHERM4 6 5 9.8
RTHERM5 5 4 19
RTHERM6 4 3 22
RTHERM7 3 2 23
RTHERM8 2 TL 24

SABER Thermal Model

Copper Area = 0.5 in²
template thermal_model th tl
thermal_c th, tl
{
ctherm.ctherm1 th 8 =1.2e-4
ctherm.ctherm2 8 7 =4.6e-3
ctherm.ctherm3 7 6 =5.0e-3
ctherm.ctherm4 6 5 =1.6e-2
ctherm.ctherm5 5 4 =4.5e-2
ctherm.ctherm6 4 3 =1.3e-1
ctherm7 3 2 6.7e-1
ctherm8 2 tl 5.5
}

rtherm.rtherm1 th 8 =1.55
rtherm.rtherm2 8 7 =1.9
rtherm.rtherm3 7 6 =2.8
rtherm.rtherm4 6 5 =9.8
rtherm.rtherm5 5 4 =19
rtherm.rtherm6 4 3 =22
rtherm.rtherm7 3 2 =23
rtherm.rtherm8 2 tl =24
}

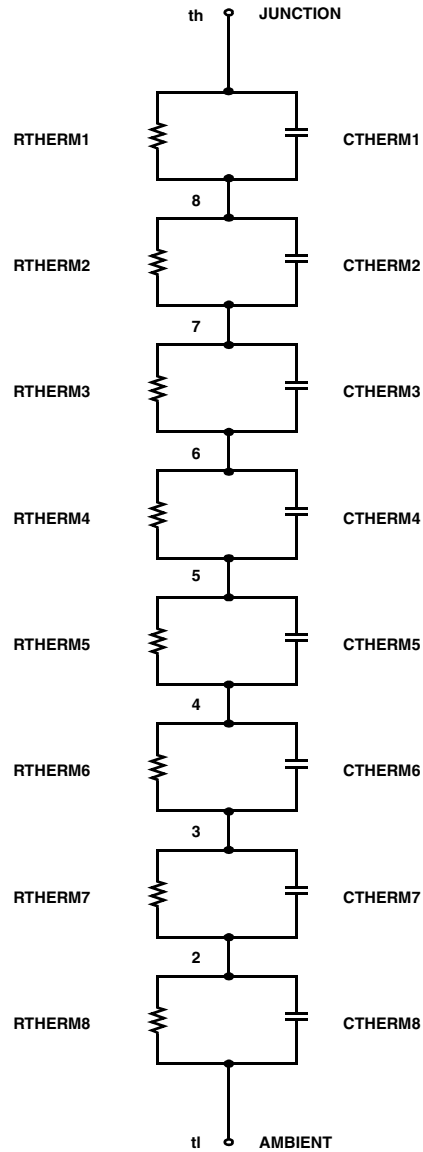


Table 1. Thermal Models

COMPONENT	0.02 in ²	0.14 in ²	0.257 in ²	0.38 in ²	0.493 in ²
CTHERM6	9.0e-1	1.3e-1	1.5e-1	1.5e-1	1.3e-1
CTHERM7	4.0e-1	6.0e-1	4.5e-1	6.5e-1	6.7e-1
CTHERM8	1.4	2.5	2.2	3.0	5.5
RTHERM6	39	26	20	20	22
RTHERM7	42	32	31	29	23
RTHERM8	48	35	38	31	24

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CoolFET [™]	FPST [™]	LittleFET [™]	PowerSaver [™]	SuperSOT [™] -6
CROSSVOLT [™]	FRFET [™]	MICROCOUPLER [™]	PowerTrench [®]	SuperSOT [™] -8
DOME [™]	GlobalOptoisolator [™]	MicroFET [™]	QFET [®]	SyncFET [™]
EcoSPARK [™]	GTO [™]	MicroPak [™]	QS [™]	TinyLogic [®]
E ² CMOS [™]	HiSeC [™]	MICROWIRE [™]	QT Optoelectronics [™]	TINYOPTO [™]
EnSigna [™]	I ² C [™]	MSX [™]	Quiet Series [™]	TruTranslation [™]
FACT [™]	i-Lo [™]	MSXPro [™]	RapidConfigure [™]	UHC [™]
		OCX [™]	RapidConnect [™]	UltraFET [®]
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The Power Franchise [®]		OPTOLOGIC [®]	SILENT SWITCHER [®]	VCX [™]
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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Rev. I15